a triggering device for breakover triggering of the main thyristor via the auxiliary thyristor and the resistance device, wherein the resistance device defines a time-dependent ohmic resistance in such a way that this resistance has a relatively large value during a switch-on phase of the main thyristor and a relatively small value during a current-carrying phase of the main thyristor.

2. (Amended) The thyristor arrangement as claimed in claim 1, wherein the resistance automatically decreases from the relatively large value to the relatively small value.

3. (Amended) The thyristor arrangement as claimed in claim 2, wherein the resistance device has an ohmic resistance of an essentially fixed value and at least one of an inductance and capacitance.

4. (Amended) The thyristor arrangement as claimed in claim 3, wherein the resistance device is a parallel circuit comprising the ohmic resistance of the essentially fixed value and the inductance or capacitance.

5. (Amended) The thyristor arrangement as claimed in claim 3, wherein the resistance device is a series circuit comprising the ohmic resistance of the essentially fixed value and the inductance or capacitance.

6. (Amended) The thyristor arrangement as claimed in claim 4, wherein the electrical anode connection is a short circuit.

7. (Amended) The thyristor arrangement as claimed in claim 5, wherein the anode connection has a series circuit comprising at least one of an inductance and capacitance and a parallel circuit comprising an ohmic resistance and at least one of a further inductance and capacitance.

8. (Amended) The thyristor arrangement as claimed in claim 1, wherein the main thyristor with its cathode and anode, the auxiliary thyristor with its cathode and anode, the resistance device, the anode connection and the triggering device are integrated on a common body made of semiconductor material.

9. (Amended) The thyristor arrangement as claimed in claim 8, wherein the resistance device includes an integrated inductance in the form of a spiral which is made of electrically conductive material and is formed on the body made of semiconductor material.

10. (Amended) The thyristor arrangement as claimed in claim 1, wherein the main thyristor with its cathode and anode is integrated on one body made of semiconductor material, and wherein the auxiliary thyristor with its cathode and anode is integrated on another body made of semiconductor material.

11. (Amended) The thyristor arrangement as claimed in claim 8, wherein the triggering device is an optical triggering device which is integrated on a body made of semiconductor material of the auxiliary thyristor.

Please add the following new claims:

-- 12. The thyristor arrangement as claimed in claim 5, wherein the electrical anode connection is a short circuit.

13. The thyristor arrangement as claimed in claim 12, wherein the anode connection has a series circuit comprising at least one of an inductance and capacitance and a parallel circuit comprising an ohmic resistance and at least one of a further inductance and capacitance.